Product data sheet

1. General description

PNP low V_{CEsat} transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350T

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat} and corresponding low R_{CEsat}
- · High collector current capability
- · High collector current gain
- Improved efficiency due to reduced heat generation
- AEC-Q101 qualified

3. Applications

- Power management applications
- Low and medium power DC/DC converters
- Supply line switching
- Battery chargers
- Linear voltage regulation with low voltage drop-out (LDO)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _C	collector current		-	-	-2	Α
I _{CRM}		$\delta \leq 0.25$; Operated under pulsed conditions; $t_p \leq 100$ ms	-	-	-3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	90	135	mΩ



50 V, 3 A PNP low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	_
2	E	emitter		C
3	С	collector		В
				E sym132
			SOT23	,

6. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
PBSS5350T	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS5350T	ZD%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-2	Α
I _{CRM}	repetitive peak collector current	$\delta \leq 0.25$; Operated under pulsed conditions; $t_p \leq 100$ ms		-	-3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-5	Α
I _B	base current			-	-0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
			[3]	-	540	mW
			[4]	-	500	mW
			[1] [5]	-	1.2	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Operated under pulsed conditions: pulse width tp \leq 100 ms, duty cycle $\delta \leq$ 0.25.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	[2] [3] [4]	[1]	-	-	417	K/W
			[2]	-	-	260	K/W
			[3]	-	-	230	K/W
			-	-	250	K/W	
			[1] [5]	-	-	104	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	75	-	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Operated under pulsed conditions: pulse width $t_p \le 100$ ms; duty cycle $\delta \le 0.25$

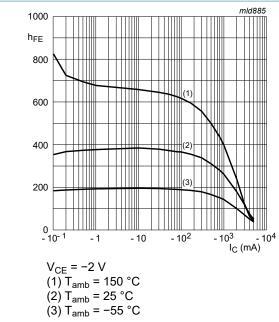
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-50	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	I_E = -100 μ A; I_C = 0 A; T_{amb} = 25 °C	-6	-	-	V
I _{СВО}	collector-base cut-off	V _{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I_{C} = -500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	130	-	-	
		V _{CE} = -2 V; I _C = -3 A; pulsed; t _p ≤ 300 µs; T _{amb} = 25 °C	80	-	-	
V _{CEsat} collector-emitter saturation voltage		I_C = -500 mA; I_B = -50 mA; pulsed; $t_p \le$ 300 μs; δ = 0.02; T_{amb} = 25 °C	-	-	-90	mV
		I_C = -1 A; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-180	mV
		I_C = -2 A; I_B = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-320	mV
		I_C = -2 A; I_B = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-270	mV
		I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-390	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	90	135	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -2 A; I_B = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-1.1	V
		I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-1.2	V
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	35	pF

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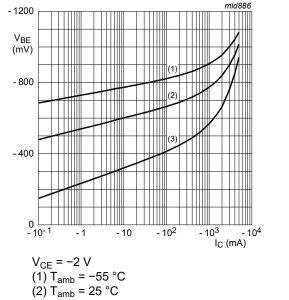


$$V_{CE} = -2 V$$
(1) $T_{---} = 150 °$

(2)
$$T_{amb} = 25 \,^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 1. DC current gain as a function of collector current; typical values

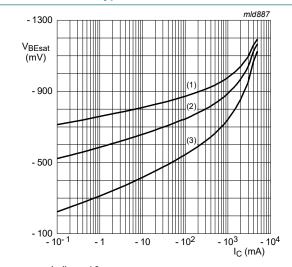


(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 2. Base-emitter voltage as a function of collector current; typical values



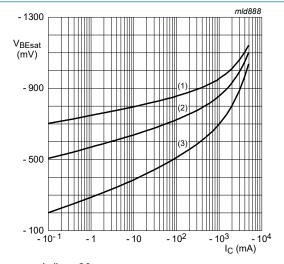
$$I_{\rm C}/I_{\rm B}=10$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

$$(2) T_{amb} = 25 °C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 3. Base-emitter saturation voltage as a function of Fig. 4. collector current; typical values



$$I_C/I_B = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Base-emitter saturation voltage as a function of collector current; typical values

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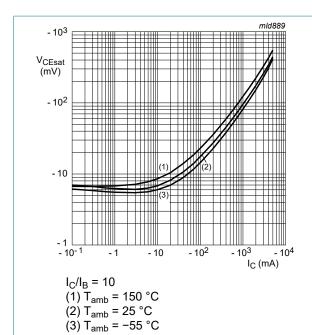


Fig. 5. Collector-emitter saturation voltage as a function of collector current; typical values

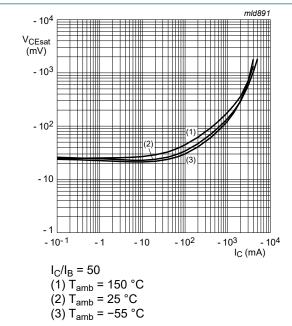


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

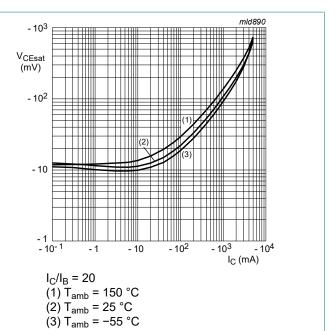
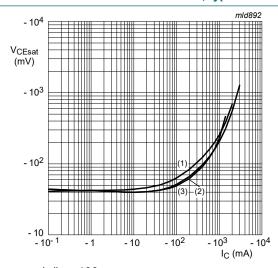


Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values

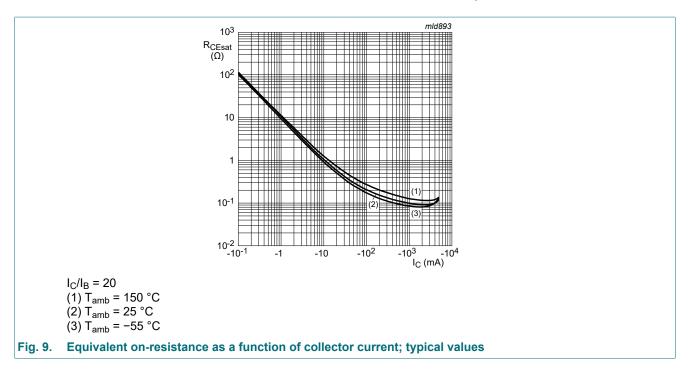


 $I_C/I_B = 100$ (1) $T_{amb} = 150 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

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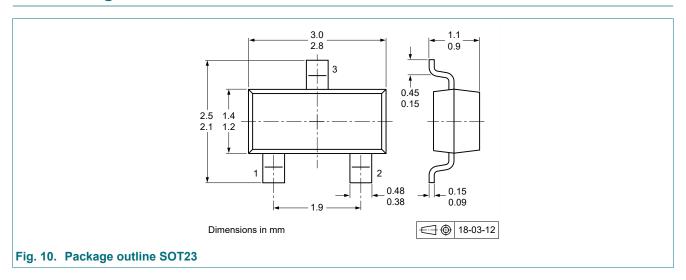


11. Test information

Quality information

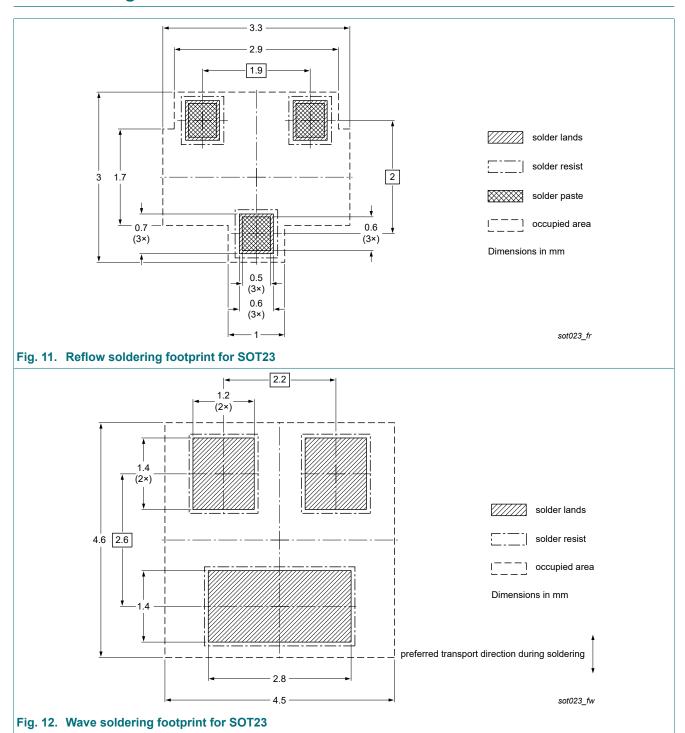
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Tubic of Itovicion motor	• 3					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5350T v.3	20220510	Product data sheet	-	PBSS5350T v.2		
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. 					
PBSS5350T v.2	20040113	Product data sheet	-	PBSS5350T v.1		
PBSS5350T v.1	20020808	Product data sheet	-	-		

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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